



#### 40V NPN LOW SATURATION TRANSISTOR IN U-DFN2020-3

#### **Features**

- BVcEo > 40V
- hfe Specified up to 3A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

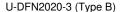
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: U-DFN2020-3 (Type B)
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208
- Weight: 0.01 grams (Approximate)

### **Applications**

- DC-DC Converters
- Charging Circuits
- Motor Control
- Power Switches

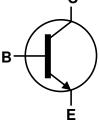


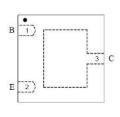


Top View



**Bottom View** 





Device Symbol

Top View Pin-Out

#### **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN5840CFDB-7	2E3	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



2E3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н			J	K		L	М		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Absolute Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	VcBo	40	
Collector-Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	
Peak Pulse Current	Ісм	7	^
Continuous Collector Current	Ic	5	A

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	D-	0.69	W	
Linear Derating Factor	(Note 6)	PD	1.25	VV	
Thermal Pagistance Junation to Ambient	(Note 5)	Б	180	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	100		
Operating and Storage Temperature Range	•	TJ, TSTG	-55 to +150	°C	

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	٧	С

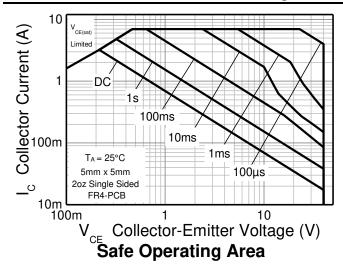
Notes:

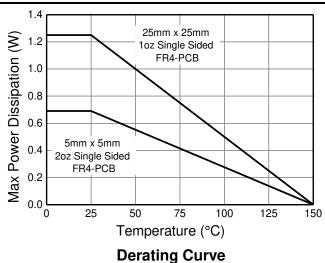
<sup>5.</sup> For a device mounted with the exposed collector on 5mm x 5mm 2oz copper on single sided FR4 PCB; device is measured under still air conditions whilst operating in the steady state.

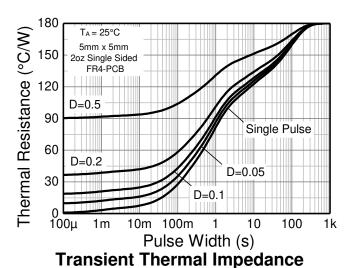
<sup>6.</sup> Same as Note (5) except the exposed collector pad is mounted on 25mm x 25mm 1oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

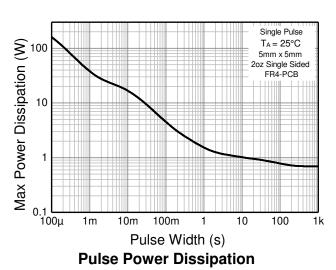


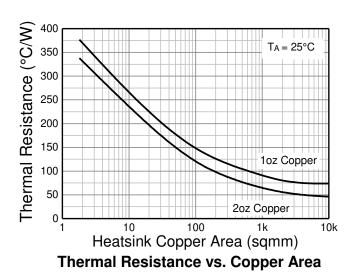
### **Thermal Characteristics and Derating Information**

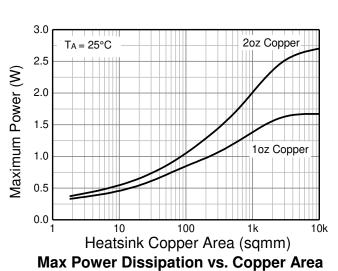














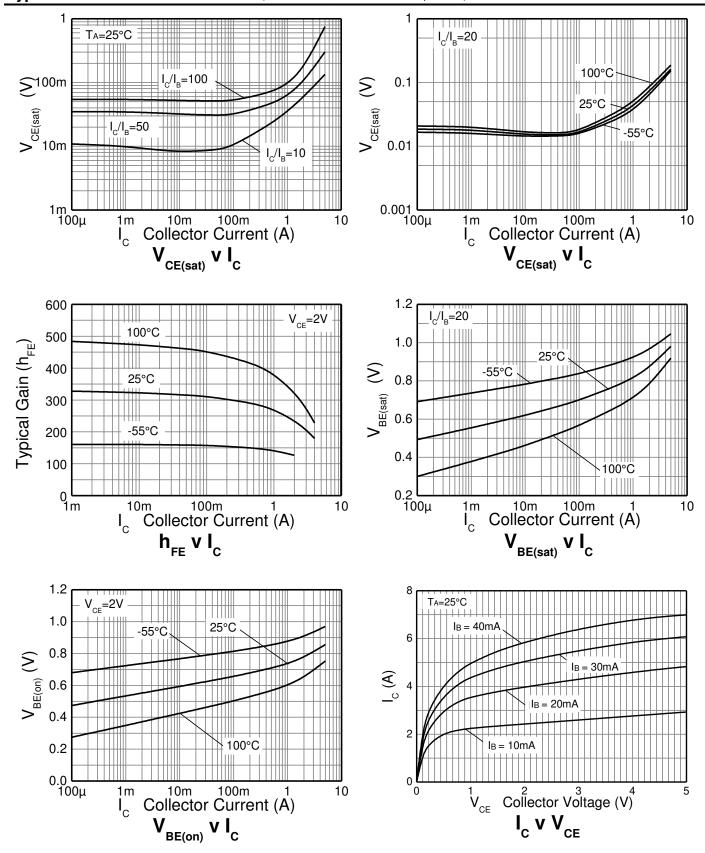
# Electrical Characteristics (@TA = +25°C, unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	40	_	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVcEo	40	_	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	_	_	V	I <sub>E</sub> = 100μA
Collector Cutoff Current	Ісво	_	_	100	nA	V <sub>CB</sub> = 40V
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	VEB = 6V
Collector Emitter Cutoff Current	Ices		_	100	nA	Vces = 32V
		200	_	_		$I_C = 10mA$ , $V_{CE} = 2V$
		200	_	_		Ic = 500mA, VcE = 2V
Static Forward Current Transfer Ratio (Note 8)	hFE	200	290	_		Ic = 1A, VcE = 2V
		190	250	_		$I_C = 2A$ , $V_{CE} = 2V$
		180	220	_		Ic = 3A, VcE = 2V
	VCE(sat)	_	10	16	- mV	Ic = 0.1A, I <sub>B</sub> = 10mA
		_	45	75		Ic = 1A, I <sub>B</sub> = 100mA
Collector-Emitter Saturation Voltage (Note 8)		_	85	145		Ic = 1A, I <sub>B</sub> = 10mA
Collector-Emitter Saturation Voltage (Note 8)		_	135	230		$I_C = 2A$ , $I_B = 20mA$
		_	195	350		Ic = 3A, I <sub>B</sub> = 30mA
		_	150	275		$I_C = 4A$ , $I_B = 400mA$
Base-Emitter Turn-On Voltage (Note 8)	V <sub>BE(on)</sub>	_	0.73	0.9	V	Ic = 2A, VcE = 2V
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(sat)</sub>	_	0.76	0.9	V	Ic = 1A, I <sub>B</sub> = 10mA
Output Capacitance	$C_obo$	_	_	70	pF	$V_{CB} = 3V$ , $f = 1MHz$
Transition Frequency	fτ	_	150	_	MHz	VcE = 5V, Ic = 0.1A, f = 100MHz
Delay Time	td	_	_	90		
Rise Time	tr	_	_	100		Vcc = 30V, Ic = 0.75A
Storage Time	ts	_	_	1050	ns	$I_{B1} = 0.1A$
Fall Time	t <sub>f</sub>	_	_	100		

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

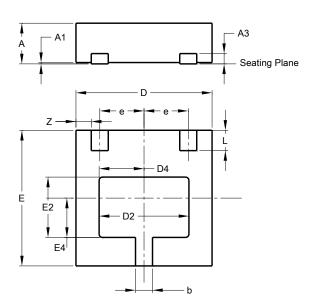




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-3 (Type B)

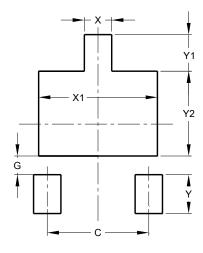


U-DFN2020-3 (Type B)						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.02			
А3	_	_	0.152			
b	0.20	0.30	0.25			
D	1.950	2.075	2.00			
D2	1.22	1.42	1.32			
D4	0.56	0.76	0.66			
Е	1.950	2.075	2.00			
E2	0.79	0.99	0.89			
E4	0.48	0.68	0.58			
е	_		0.65			
L	0.25	0.35	0.30			
Z		_	0.225			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-3 (Type B)



Dimensions	Value (in mm)
C	1.300
G	0.240
X	0.350
X1	1.520
Υ	0.500
Y1	0.470
Y2	1.090



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